

### **isc Silicon NPN Power Transistor**

# **BD743**

### DESCRIPTION

- Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 45V(Min)
- Collector Power Dissipation-
- : Pc= 90W@ Ic= 25℃
- 15A Continuous Collector Current
- Complement to Type BD744
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

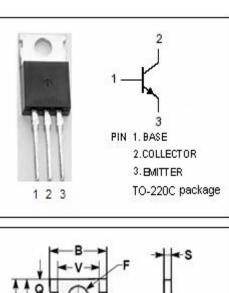
• Designed for use in general purpose power amplifier and switching applications.

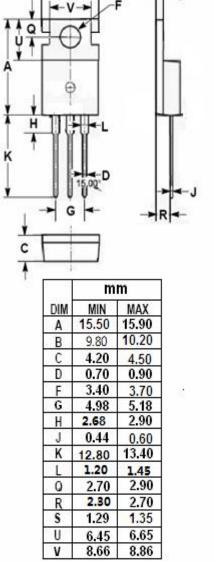
#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	50	v	
V <sub>CEO</sub>	Collector-Emitter Voltage 45		V	
V <sub>EBO</sub>	Emitter-Base Voltage	5		
lc	Collector Current-Continuous 15		А	
I <sub>CM</sub>	Collector Current-Peak	20	А	
IB	Base Current-Continuous	5	А	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃	2	w	
	Collector Power Dissipation @ $T_c=25^{\circ}C$	90		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C	

#### **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.4	°C/W
R <sub>th j-a</sub>	R <sub>th j-a</sub> Thermal Resistance, Junction to Ambient		°C/W





isc website: <u>www.iscsemi.com</u>



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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	45		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A		1.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 5A		3.0	V
V <sub>BE(on)-1</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 4V		1.0	V
V <sub>BE(on)-2</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 15A ; V <sub>CE</sub> = 4V		3.0	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 50V; I <sub>E</sub> = 0		0.1	mA
		V <sub>CB</sub> = 50V; I <sub>E</sub> = 0; T <sub>C</sub> = 125°C		5.0	
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> = 0		0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		0.5	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 4V	40		
h <sub>FE-2</sub>	DC Current Gain	Ic= 5A ; Vce= 4V	20	150	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 15A ; V <sub>CE</sub> = 4V	5		

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